

*CLAIM AMENDMENTS*

1. (Currently Amended) A method for manufacturing a semiconductor device having a gate electrode comprising ~~the steps of:~~

forming a gate insulating film on a substrate;

forming an electrode-constituting film for constituting ~~the~~ a gate electrode on the gate insulating film,

forming a silicon nitride film on the electrode-constituting film;

forming a mask film on the silicon nitride film;

forming a resist pattern on the mask film;

patterning the mask film using the resist pattern as a mask to form a patterned mask film;

patterning the silicon nitride film and the electrode-constituting film by dry etching using ~~a~~ the patterned mask film as a mask; and

removing the mask film by ~~CMP~~ chemical-mechanical polishing (CMP), using the silicon nitride film as a stopper film, after patterning the electrode-constituting film.

2. (Currently Amended) The method for manufacturing a semiconductor device according to claim 1 further comprising ~~the steps of:~~

forming an interlayer insulating film after patterning the electrode-constituting film;

forming contact holes in the interlayer insulating film; ~~and~~

forming a conductive film ~~on over all of the entire surface of the~~ substrate, including in the contact holes, wherein contact plugs are formed in the contact holes in the interlayer insulating film; ~~and~~

removing the mask film is, simultaneously removed in said step of with removing the mask film by CMP, using the silicon nitride film as a stopper film.

3. (Currently Amended) The method for manufacturing a semiconductor device according to claim 2, wherein the ~~material of the~~ mask film is the same as the material of as the contact plugs.

4. (Currently Amended) The method for manufacturing a semiconductor device according to claim 1, further comprising ~~the step of~~ forming wirings on the silicon nitride film after removing the mask film.

5. (Currently Amended) A method for manufacturing a semiconductor device having a gate electrode comprising ~~the steps of~~:

- forming a gate insulating film on a substrate;
- forming an electrode-constituting film for constituting ~~the~~ a gate electrode on the gate insulating film;
- forming a silicon nitride film on the electrode-constituting film;
- forming a mask film ~~using~~ of the same material as the material of the electrode-constituting film, on the silicon nitride film;
- forming a resist pattern on the mask film;
- patterning the mask film using the resist pattern as a mask to form a patterned mask film; and
- patterning the silicon nitride film and the electrode-constituting film, and, simultaneously, removing the mask film, by dry etching, using ~~a~~ the patterned mask film as a mask.

6. (Currently Amended) The method for manufacturing a semiconductor device according to claim 5, further comprising ~~a step for~~ forming wirings on the patterned silicon nitride film.